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# **Quantum Dot Solar Cells with Multiple Exciton Generation**

M.C. Hanna, M.C. Beard, J.C. Johnson, J. Murphy, R.J. Ellingson, and A.J. Nozik

Presented at the 2005 DOE Solar Energy Technologies Program Review Meeting November 7–10, 2005 Denver, Colorado Conference Paper NREL/CP-590-38992 November 2005



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# **Quantum Dot Solar Cells with Multiple Exciton Generation**

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#### **ABSTRACT**

We have measured the quantum yield of the multiple exciton generation (MEG) process in quantum dots (QDs) of the lead-salt semiconductor family (PbSe, PbTe, and PbS) using fs pump-probe transient absorption measurements. Very high quantum yields (up to 300%) for charge carrier generation from MEG have been measured in all of the Pb-VI QDs. We have calculated the potential maximum performance of various MEG QD solar cells in the detailed balance limit. We examined a two-cell tandem PV device with singlet fission (SF), QD, and normal dve (N) absorbers in the nine possible series-connected combinations to compare the tandem combinations and identify the combinations with the highest theoretical efficiency. We also calculated the maximum efficiency of an idealized single-gap MEG QD solar cell with M multiplications and its performance under solar concentration.

### 1. Objectives

The objective of this continuing project is to explore the possibility of greatly enhanced conversion efficiency in third-generation PV cells based on charge multiplication from the process of multiple exciton generation (MEG) in low-bandgap semiconductor quantum dots (QDs).

#### 2. Technical Approach

We use fs pump-probe transient absorption dynamics to study carrier relaxation and MEG processes in QDs. For efficiency calculations, we use a detailed-balance model in which we assume complete light absorption for photon energy greater than the absorption threshold, charge multiplication occurs by MEG or singlet fission (SF), all photogenerated carriers are collected, and the only loss mechanism is due to spontaneous radiative recombination.

# 3. Results and Accomplishments

Extending our previous measurements of high MEG quantum yield in PbSe QDs, we found similar MEG quantum efficiencies in PbS and PbTe QDs. The quantum yield reached 300% at 4 x Eg, where Eg is the bandgap of the QD.

We have generalized our model for calculating the maximum efficiency of an idealized MEG QD solar cell to include M multiplications and the expected performance under solar concentration. For a given bandgap, Eg, the maximum number of excitons, Mmax, that can be produced per photon by MEG is

dictated by energy conservation considerations. The value of Mmax is given by Mmax = Emax/Eg, where  $Emax \sim 4.4$  eV is the highest photon energy in the AM1.5 solar spectrum. As an example, for Eg = 0.75 eV, Eg = 0.75

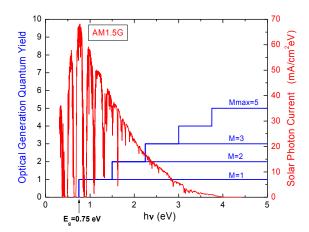


Fig. 1. MEG quantum yield models for Eg = 0.75 eV overlapping the AM1.5G spectrum. The maximum possible multiplication for this bandgap is Mmax = 5.

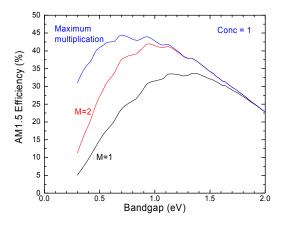


Fig. 2. Maximum efficiency at one sun for a MEG QD solar cell versus bandgap for multiplications of M = 1, 2, and Mmax.

The calculated efficiency versus bandgap for a MEG cell with  $M=1,\ 2,\ and\ Mmax$  under one sun concentration is shown in Fig. 2. Allowing the maximum possible multiplication in a MEG cell raises the ultimate efficiency only a small amount compared to M=2 (from 42.0% at Eg = 0.95 eV to 44.4% at Eg = 0.7 eV). In general, cells with lower bandgap benefit more from allowing maximum multiplication. Figure 3

shows how the maximum efficiency of a MEG cell with maximum multiplication changes with concentration. The maximum possible efficiency at maximum multiplication is 84.9% at a bandgap of 0.05 eV.

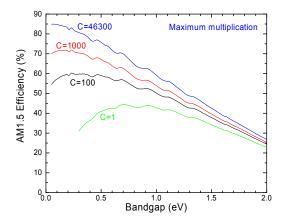


Fig. 3. Maximum efficiency versus bandgap of a MEG QD cell with maximum allowable exciton multiplication for different solar concentrations.

We have calculated the upper limits on the maximum efficiency of a two-gap tandem PV device with various combinations of a MEG QD absorber, a normal dye absorber (N), or an SF absorber as the top and bottom cells to identify the combinations with the highest theoretical efficiency. The efficiencies were calculated in the detailed-balance limit with the top and bottom cells electrically and optically in series.

The N-absorber generates one electron-hole (e-h) pair per photon absorbed above the bandgap. The QD-absorber generates two e-h pairs for photons with energy greater than twice the bandgap and one e-h pair for photons with energy between one and two times the bandgap. An ideal SF absorber has a triplet state ( $E_T = E_1$ ) and a singlet state ( $E_S = 2 \times E_1$ ). The SF-absorber absorbs all photons with energy above the singlet state at twice the triplet state energy ( $E_T =$  bandgap) and generates two electrons per absorbed photon for photons in this energy range.

The maximum overall efficiency, along with the optimum bandgaps of the top and bottom cells for each of the nine possible combinations, is summarized in Table 1. The best absorber combinations, (SF,QD), (QD,N), (QD,QD), and (QD,SF), have a QD-absorber as the top cell or the bottom cell. These cells have a potential efficiency of greater than 47% for one sun illumination, which exceeds the value of 45.7% for the usual (N,N) tandem.

Table 1. Maximum AM1.5G theoretical efficiency for SF, QD, and N tandem cell combinations at the optimum top and bottom cell bandgaps.

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Top/Bottom	Top Cell	Bottom Cell	Maximum					
Absorber	Bandgap	Bandgap	Efficiency					
	(eV)	(eV)	(%)					
(N,N)	1.63	0.95	45.7 45.7					
(N,QD)	1.61	0.95						
(N,SF)	1.39	0.48	43.8 47.1 47.6 47.3					
(QD,N)	1.63	0.95						
(QD,QD)	1.46	0.68						
(QD,SF)	1.40	0.48						
(SF,N)	0.95	0.95	45.4 47.7					
(SF,QD)	0.84	0.70						
(SF,SF)	0.82	0.48	45.7					

#### 4. Conclusions

We have measured very high MEG quantum yields (up to 300%) for charge carrier generation in Pb-VI QDs (VI = S, Se, Te). We have calculated the maximum attainable efficiencies of both single-gap and two-gap tandem cells that incorporate MEG QD absorbers. Future work will focus on studying the MEG process in other QD materials, producing information on charge transfer and optical properties of QD/TiO $_2$  composites, and modeling the electrical behavior and potential performance of MEG QD solar cells.

#### **ACKNOWLEDGEMENTS**

M.C. Hanna was supported by the NREL NCPV Solar Program. M.C. Beard, J.C. Johnson, R.J. Ellingson, J. Murphy, and A.J. Nozik were supported by the DOE Office of Science, Basic Energy Sciences, Division of Chemical Sciences. NREL work is performed under DOE contract DE-AC36-99-GO10337.

# **MAJOR FY 2005 PUBLICATIONS**

R.J. Ellingson, M.C. Beard, J.C. Johnson, P. Yu, O.I. Micic, A.J. Nozik, A. Shabaev, and A.L. Efros, "Highly Efficient Multiple Exciton Generation in Colloidal PbSe and PbS Quantum Dots," *Nano Letters* **5**, 865 (2005).

# REPORT DOCUMENTATION PAGE

Form Approved OMB No. 0704-0188

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1.			EPORT TYPE			3. DATES COVERED (From - To)		
	November 2005	С	onference Paper	•	_			
4.	TITLE AND SUBTITLE					ITRACT NUMBER		
	Quantum Dot Solar Cells with Multiple Exciton Generation			DE-AC36-99-GO10337				
					5b. GRANT NUMBER			
				5c. PRO	5c. PROGRAM ELEMENT NUMBER			
6.	6. AUTHOR(S) M.C. Hanna, M.C. Beard, J.C. Johnson, J. Murphy, R.J. Ellingson,			5d. PROJECT NUMBER				
				NREL/CP-590-38992				
	and A.J. Nozik				5e. TASK NUMBER			
					PVA6.0605			
					5f. WORK UNIT NUMBER			
7.	PERFORMING ORGANIZATION NA	ME(S)	AND ADDRESS(ES)			8. PERFORMING ORGANIZATION		
	National Renewable Energy L	₋aborat	ory			REPORT NUMBER		
	1617 Cole Blvd.		•			NREL/CP-590-38992		
	Golden, CO 80401-3393							
9.	9. SPONSORING/MONITORING AGENCY NAME(S) AND ADDRESS(ES)				10. SPONSOR/MONITOR'S ACRONYM(S)			
						NREL		
						44 000000000000000000000000000000000000		
					11. SPONSORING/MONITORING AGENCY REPORT NUMBER			
						AGENOT KET GRY NOMBER		
12	DISTRIBUTION AVAILABILITY STA	TEMEN	т					
12.	National Technical Information Service							
	U.S. Department of Commerce							
	5285 Port Royal Road							
	Springfield, VA 22161							
13. SUPPLEMENTARY NOTES								
14.	ABSTRACT (Maximum 200 Words)							
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combinations with the highest theoretical efficiency. We also calculated the maximum efficiency of an idealized								
	single-gap MEG QD solar cell with M multiplications and its performance under solar concentration.							
15. SUBJECT TERMS								
Photovoltaics; solar; quantum dot solar cells; PV; NREL								
16.	SECURITY CLASSIFICATION OF:		17. LIMITATION	18. NUMBER	19a. NAME C	OF RESPONSIBLE PERSON		
	a. REPORT b. ABSTRACT c. THIS PAGE OF ABSTRACT OF PAGES							
Ur	nclassified Unclassified Uncla	ssified	UL		19b. TELEPO	ONE NUMBER (Include area code)		